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TinyLogic ULP-A Buffer with Three-State Output

NC7SV126

The NC7SV126 is a single 3–State buffer in tiny footprint packages. The device is designed to operate for V_{CC} = 0.9 V to 3.6 V.

Features

- Designed for 0.9 V to 3.6 V V_{CC} Operation
- 1.8 ns t_{PD} at 3.3 V (Typ)
- Inputs/Outputs Over–Voltage Tolerant up to 3.6 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.3 V
- Available in SC/SC–88A and MicroPak™ Packages
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

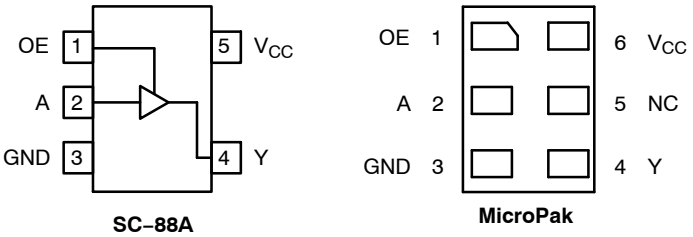

Figure 1. Pinout (Top View)

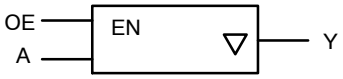

Figure 2. Logic Symbol

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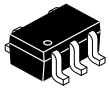
MARKING DIAGRAM

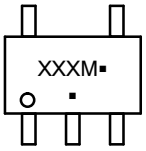
SIP6 1.45 x1.0 MicroPak CASE 127EB

CC = Specific Device Code
KK = 2–Digit Lot Run Traceability Code
XY = 2–Digit Date Code
Z = Assembly Plant Code

MARKING DIAGRAM



SC–88A CASE 419A–02



XXX = Specific Device Code
M = Date Code
▪ = Pb–Free Package

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

PIN ASSIGNMENT

Pin	SC88A	MicroPak
1	OE	OE
2	A	A
3	GND	GND
4	Y	Y
5	V_{CC}	NC
6	–	V_{CC}

FUNCTION TABLE

Input		Output
OE	**A**	**Y**
H	L	L
H	H	H
L	X	Z

X = Don't Care

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +4.3	V
V_{IN}	DC Input Voltage		−0.5 to +4.3	V
V_{OUT}	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +4.3 −0.5 to +4.3	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−50	mA
I_{OUT}	DC Output Source/Sink Current		±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±50	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC−88A MicroPak	377 154	°C/W
P_D	Power Dissipation in Still Air	SC−88A MikroPak	332 812	mW
MSL	Moisture Sensitivity		Level 1	−
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow per JESD51−7.
3. HBM tested to EIA / JESD22−A114−A. CDM tested to JESD22−C101−A. JEDEC recommends that ESD qualification to EIA/JESD22−A115A (Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	DC Input Voltage		0	3.6	V
V_{OUT}	DC Output Voltage	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 3.6 3.6	
T_A	Operating Temperature Range		−40	+85	°C
t_r , t_f	Input Transition Rise and Fall Time	V_{CC} = 3.3 V ±0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		0.9	_	0.5	–	_	–	V
			1.1 to 1.3	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	
			1.4 to 1.6	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	
			1.65 – 1.95	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	
			2.3 to < 2.7	1.6	–	–	1.6	–	
			2.7 to 3.6	2.0	–	–	2.0	–	
V_{IL}	Low−Level Input Voltage		0.9	–	0.5	–	–	–	V
			1.1 to 1.3	–	–	0.35 x V_{CC}	–	0.35 x V_{CC}	
			1.4 to 1.6	–	–	0.35 x V_{CC}	–	0.35 x V_{CC}	
			1.65 – 1.95	–	–	0.35 x V_{CC}	–	0.35 x V_{CC}	
			2.3 to < 2.7	–	–	0.7	–	0.7	
			2.7 to 3.6	–	–	0.8	–	0.8	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}							V
		I_{OH} = −100 μA	0.9	–	V_{CC} − 0.1	–	–	–	
			1.1 to 3.6	V_{CC} − 0.1	–	–	V_{CC} − 0.1	–	
			1.4 to 1.6	V_{CC} − 0.1	–	–	V_{CC} − 0.1	–	
			1.65 to 1.95	V_{CC} − 0.2	–	–	V_{CC} − 0.2	–	
			2.3 to < 2.7	V_{CC} − 0.2	–	–	V_{CC} − 0.2	–	
			2.7 to 3.6	V_{CC} − 0.2	–	–	V_{CC} − 0.2	–	
		I_{OH} = −2 mA	1.1 o 1.3	0.75 x V_{CC}	–	–	0.75 x V_{CC}	–	
		I_{OH} = −4 mA	1.4 to 1.6	0.75 x V_{CC}	–	–	0.75 x V_{CC}	–	
		I_{OH} = −6 mA	1.65 to 1.95	1.25	–	–	1.25	–	
			2.3 to < 2.7	2.0	–	–	2.0	–	
		I_{OH} = −12 mA	2.3 to < 2.7	1.8	–	–	1.8	–	
			2.7 to 3.6	2.2	–	–	2.2	–	
		I_{OH} = −18 mA	2.3 to < 2.7	1.7	–	–	1.7	–	
			2.7 to 3.6	2.4	–	–	2.4	–	
		I_{OH} = −24 mA	2.7 to 3.6	2.2	–	–	2.2	–	
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}							V
		I_{OL} = 100 μA	0.9	–	0.1	–	–	–	
			1.1 to 3.6	–	–	0.1	–	0.1	V
			1.4 to 1.6	–	–	0.1	–	0.1	V
			1.65 to 1.95	–	–	0.2	–	0.2	V
			2.3 to < 2.7	–	–	0.2	–	0.2	V
			2.7 to 3.6	–	–	0.2	–	0.2	V
		I_{OL} = 2 mA	1.1 o 1.3	–	–	0.25 x V_{CC}	–	0.25 x V_{CC}	V
		I_{OL} = 4 mA	1.4 to 1.6	–	–	0.25 x V_{CC}	–	0.25 x V_{CC}	V
		I_{OL} = 6 mA	1.65 to 1.95	–	–	0.3	–	0.3	
		I_{OL} = 12 mA	2.3 to < 2.7	–	–	0.4	–	0.4	
			2.7 to 3.6	–	–	0.4	–	0.4	
		I_{OL} = 18 mA	2.3 to < 2.7	–	–	0.6	–	0.6	
			2.7 to 3.6	–	–	0.4	–	0.4	
		I_{OL} = 24 mA	2.7 to 3.6	–	–	0.55	–	0.55	

DC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
I_{IN}	Input Leakage Current	V_{IN} = 3.6 V or GND	0.9 to 3.6	–	–	±0.1	–	±0.5	μA
I_{OZ}	3−State Output Leakage Current	V_{OUT} = 0 V to 3.6 V	0.9 to 3.6	–	–	±0.5	–	±0.5	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 3.6 V or V_{OUT} = 3.6 V	0	–	–	0.5	–	0.5	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	0.9 to 3.6	–	–	0.9	–	0.9	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

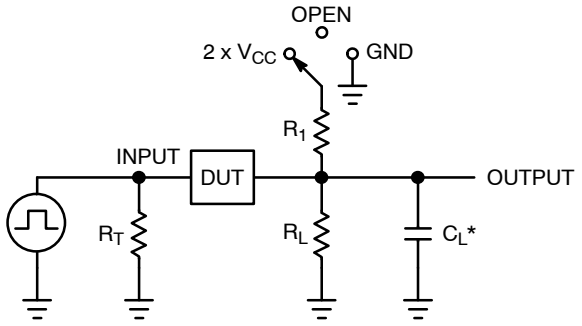
AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A to Y (Figures 3 and 4)	R_L = 1 MΩ, C_L = 15 pF	0.9	–	17.6	–	–	–	ns
		R_L = 2 kΩ, C_L = 15 pF	1.10 to 1.30	–	6.3	12.6	–	14.9	
			1.40 to 1.60	–	3.8	5.3	–	5.7	
		R_L = 500 Ω, C_L = 30 pF	1.65 to 1.95	–	3.0	4.3	–	4.6	
			2.3 to 2.7	–	2.1	2.8	–	3.0	
			2.7 to 3.6	–	1.8	2.6	–	2.8	
t_{PZH}, t_{PZL}	Output Enable Time, OE to Y (Figures 3 and 4)	C_L = 30 pF R_1 = R_L = 1 kΩ	0.9	–	19.7	–	–	–	ns
			1.10 to 1.30	–	6.0	9.7	–	16.4	
			1.40 to 1.60	–	3.5	6.0	–	7.5	
			1.65 to 1.95	–	2.7	4.5	–	5.0	
			2.3 to 2.7	–	2.0	3.0	–	3.4	
			2.7 to 3.6	–	1.7	2.6	–	2.9	
t_{PHZ}, t_{PLZ}	Output Disable Time, OE to Y (Figures 3 and 4)	C_L = 30 pF R_1 = R_L = 1 kΩ	0.9	–	10.3	–	–	–	ns
			1.10 to 1.30	–	4.9	9.5	–	14.0	
			1.40 to 1.60	–	3.3	5.5	–	7.0	
			1.65 to 1.95	–	3.0	5.6	–	5.8	
			2.3 to 2.7	–	2.5	4.2	–	5.0	
			2.7 to 3.6	–	2.9	3.9	–	4.2	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition	Typical (T_A = 25°C)	Unit
C_{IN}	Input Capacitance	V_{CC} = 0 V	2.0	pF
C_{OUT}	Output Capacitance	V_{CC} = 0 V	4.5	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 0.9 to 3.6 V, V_{IN} = 0 V or V_{CC}	20	pF

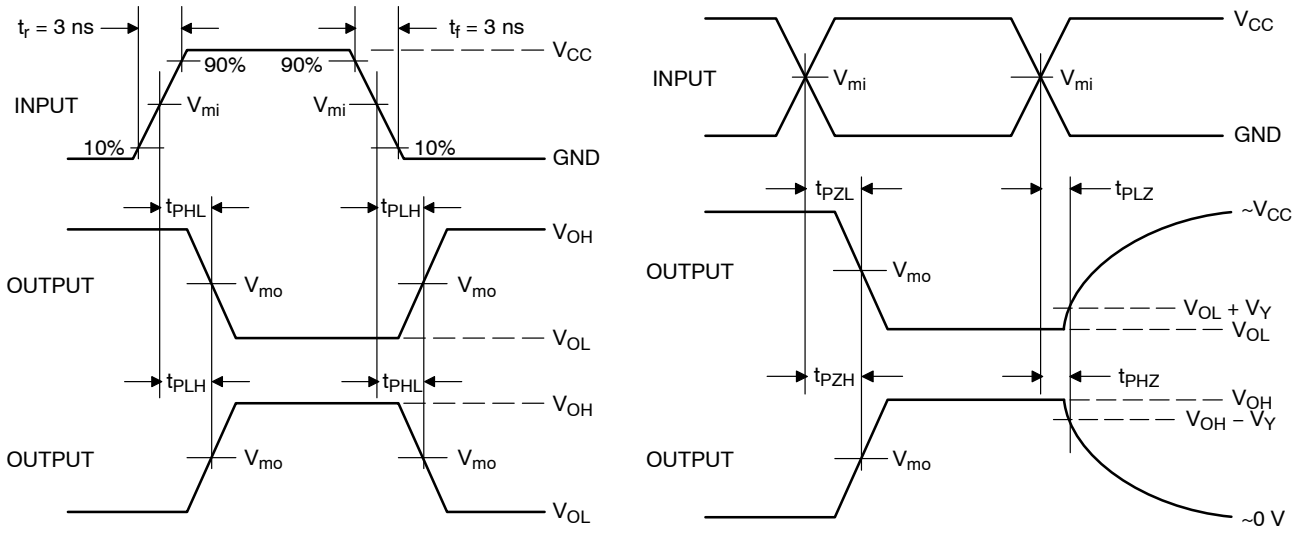
5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption: $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position
t_{PLH} / t_{PHL}	Open
t_{PLZ} / t_{PZL}	2 x V_{CC}
t_{PHZ} / t_{PZH}	GND

C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Figure 3. Test Circuit



V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
0.9	V_{CC} / 2	V_{CC} / 2	V_{CC} / 2	0.1
1.1 to 1.3	V_{CC} / 2	V_{CC} / 2	V_{CC} / 2	0.1
1.4 to 1.6	V_{CC} / 2	V_{CC} / 2	V_{CC} / 2	0.1
1.65 to 1.95	V_{CC} / 2	V_{CC} / 2	V_{CC} / 2	0.15
2.3 to 2.7	V_{CC} / 2	V_{CC} / 2	V_{CC} / 2	0.15
3.0 to 3.6	1.5	1.5	1.5	0.3

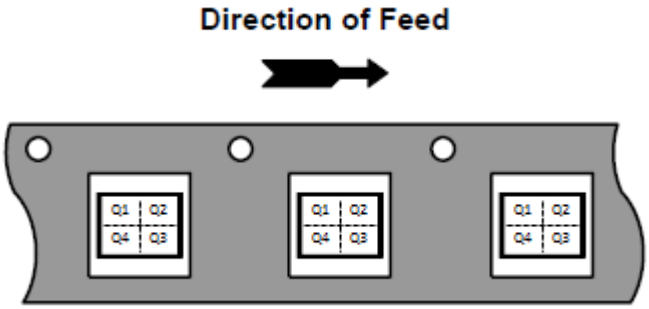
Figure 4. Switching Waveforms

ORDERING INFORMATION

Device	Package	Marking	Pin 1 Orientation (See below)	Shipping†
NC7SV126P5X	SC−88A	V26	Q4	3000 / Tape & Reel
NC7SV126L6X	MicroPak	H7	Q4	5000 / Tape & Reel

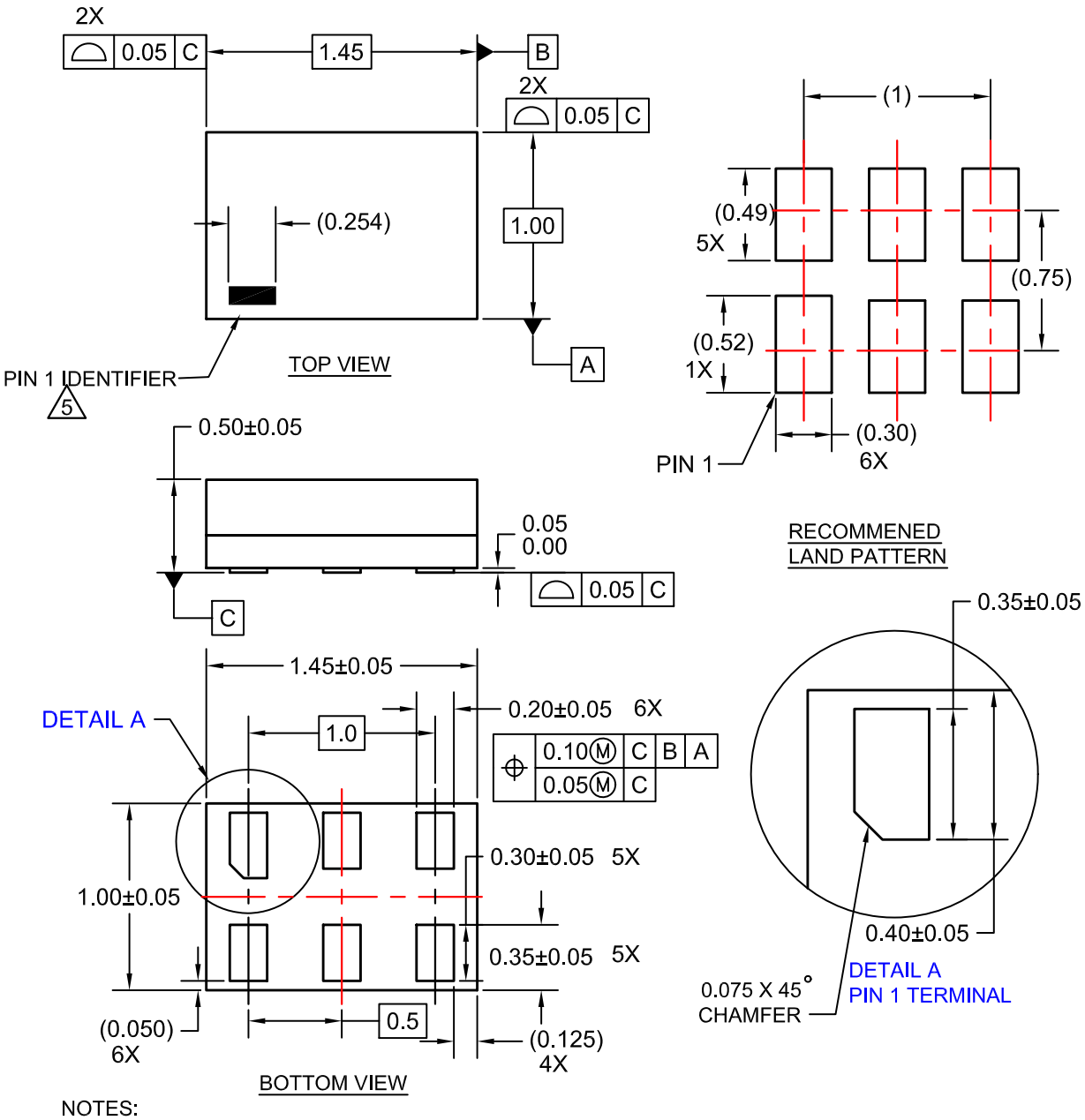
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel



PACKAGE DIMENSIONS

SIP6 1.45X1.0
CASE 127EB
ISSUE O

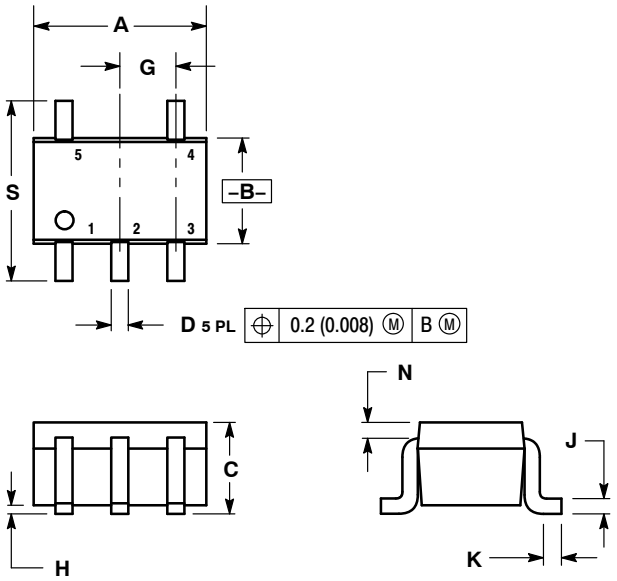


NOTES:

1. CONFORMS TO JEDEC STANDARD MO-252 VARIATION UAAD
2. DIMENSIONS ARE IN MILLIMETERS
3. DRAWING CONFORMS TO ASME Y14.5M-2009
4. PIN ONE IDENTIFIER IS 2X LENGTH OF ANY OTHER LINE IN THE MARK CODE LAYOUT.

PACKAGE DIMENSIONS

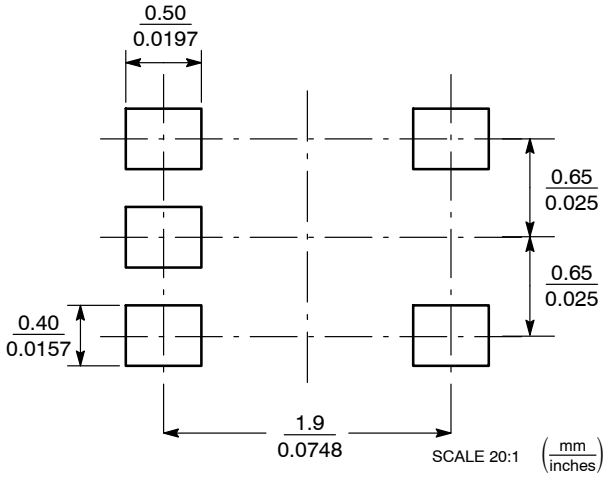
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L



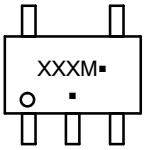
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDER FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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